

isc Silicon NPN Power Transistor

2SC2577

DESCRIPTION

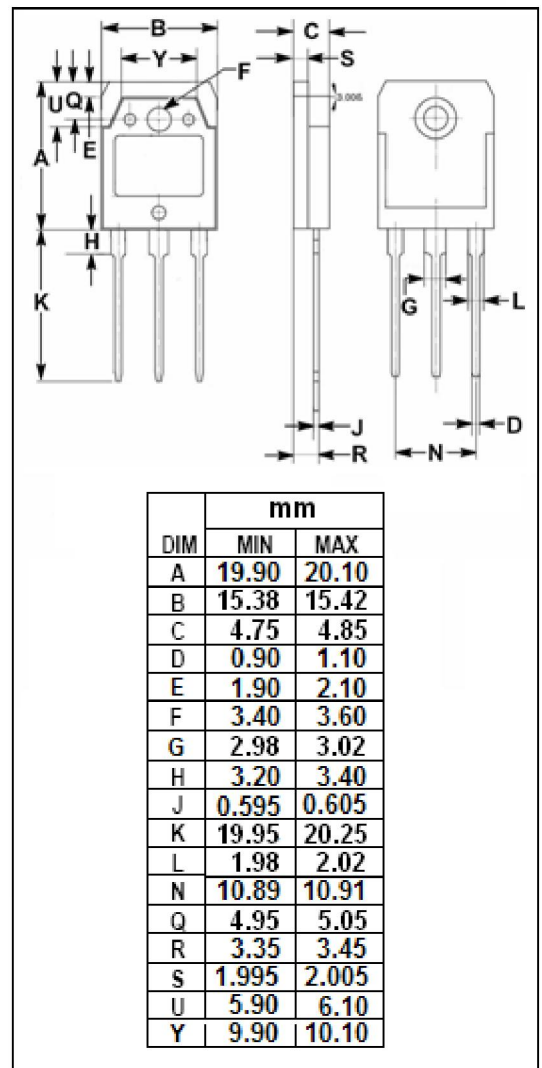
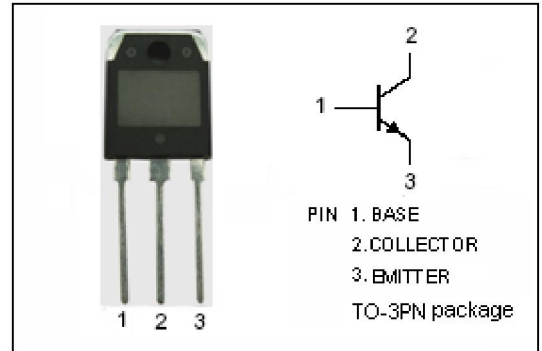
- Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = 80V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SA1102

APPLICATIONS

- Designed for audio power amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	6	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation @ $T_c=25^{\circ}C$	60	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SC2577****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			10	μA
h_{FE}	DC Current Gain	$I_C=2\text{A}; V_{CE}=4\text{V}$	50			
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1.0\text{MHz}$		110		pF
f_T	Current-Gain—Bandwidth Product	$I_E=-0.5\text{A}; V_{CE}=12\text{V}$		20		MHz

◆ **h_{FE} Classifications**

O	P	Y
50-100	70-140	90-180